Elektronische Bauelemente

MMBTA92

PNP Silicon

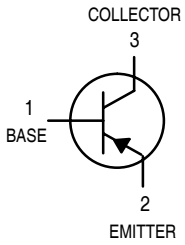
General Purpose Transistor

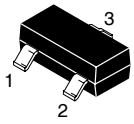
RoHS Compliant Product

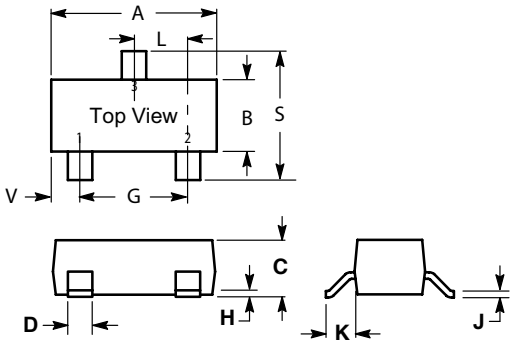
A suffix of "-C" specifies halogen & lead-free

FEATURES

- Pb-free is available.
- Power dissipation & Collector current
  Pcm: 0.3W Icm: -0.3A
- High voltage $V_{(BR)}$: -300V







SOT-23		
Dim	**Min**	**Max**
A	2.800	3.040
B	1.200	1.400
C	0.890	1.110
D	0.370	0.500
G	1.780	2.040
H	0.013	0.100
J	0.085	0.177
K	0.450	0.600
L	0.890	1.020
S	2.100	2.500
V	0.450	0.600
All Dimension in mm		

ELECTRICAL CHARACTERISTICS Tamb=25 ℃ unless otherwise specified

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	Ic= -100uA, I_E=0	-300		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	Ic= -1 mA, I_B=0	-300		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E= -100uA, I_C=0	-5		V
Collector cut-off current	I_{CBO}	V_{CB}=-200 V , I_E=0		-0.25	μ A
Emitter cut-off current	I_{EBO}	V_{EB}= -5V , I_C=0		-0.1	μ A
DC current gain	$H_{FE\ (1)}$	V_{CE}= -10V, I_C= - 1mA	60		
	$H_{FE\ (2)}$	V_{CE}= -10V, I_C=-10mA	100	200	
	$H_{FE\ (3)}$	V_{CE}=-10V, I_C=-30mA	60		
Collector-emitter saturation voltage	V_{CE}(sat)	I_C=-20 mA, I_B= -2mA		-0.2	V
Base-emitter saturation voltage	V_{BE}(sat)	I_C= -20 mA, I_B=-2mA		-0.9	V
Transition frequency	f_T	V_{CE}=-20V, I_C=-10mA f=30MHz	50		MHz

DEVICE MARKING

MMBTA92=2D

MMBTA92

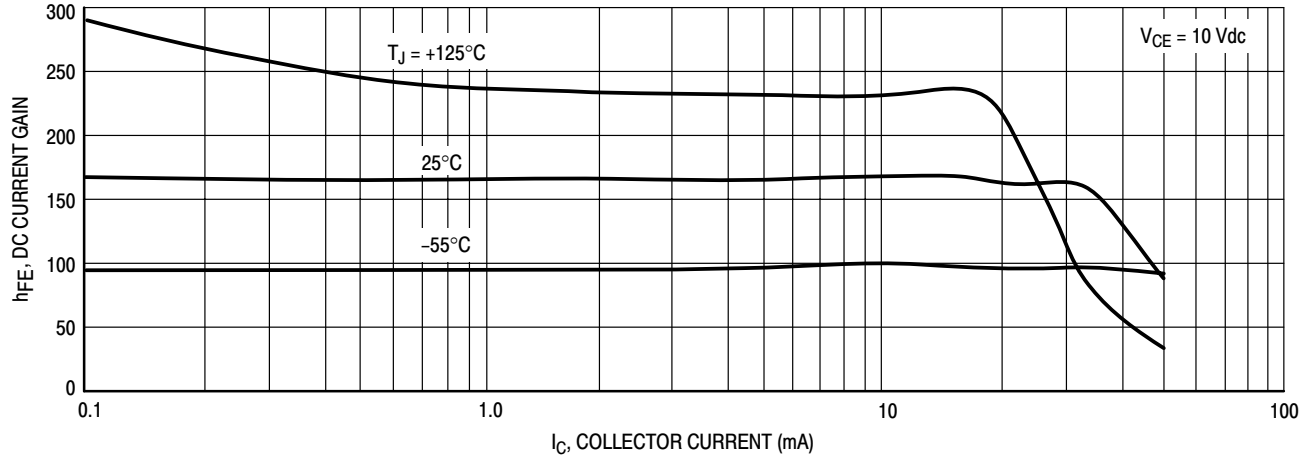


Figure 1. DC Current Gain

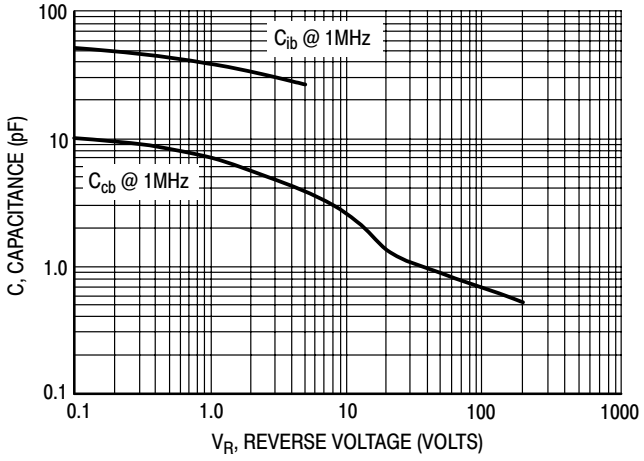


Figure 2. Capacitance

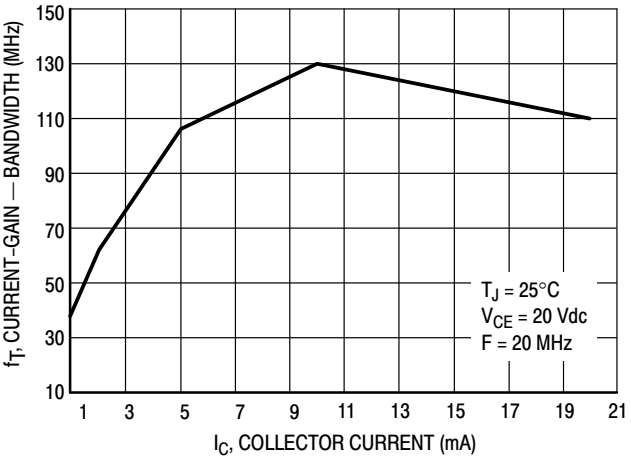
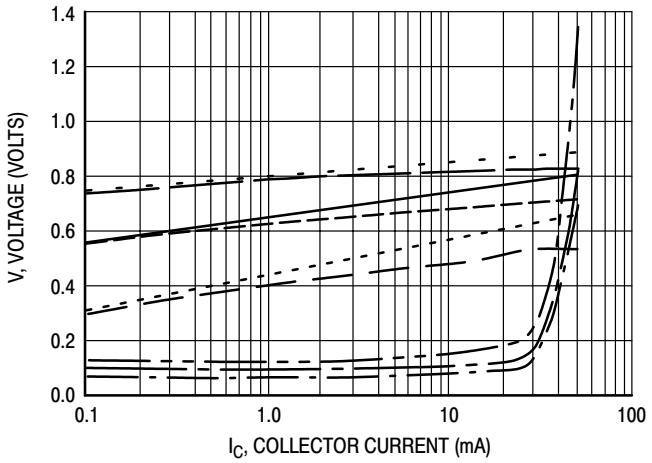


Figure 3. Current–Gain – Bandwidth



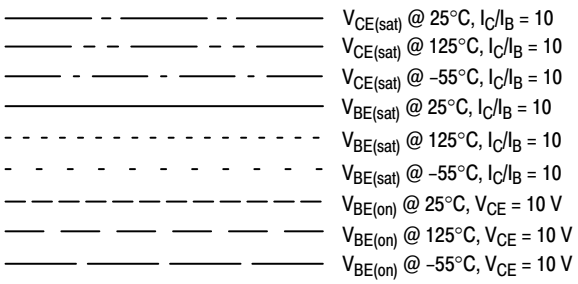


Figure 4. "ON" Voltages